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FIG. 1A

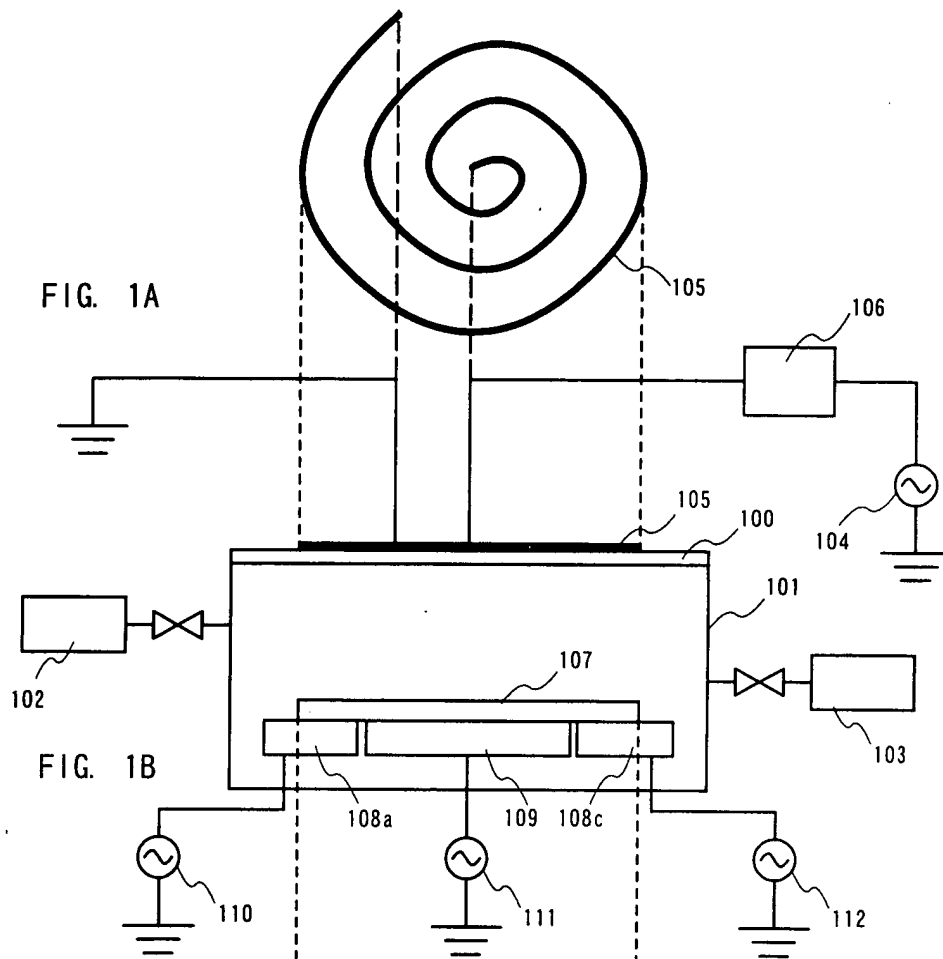


FIG. 1B

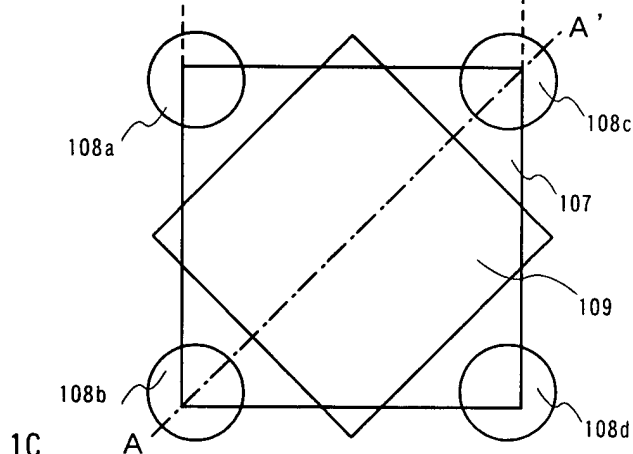


FIG. 1C

FIG. 2A

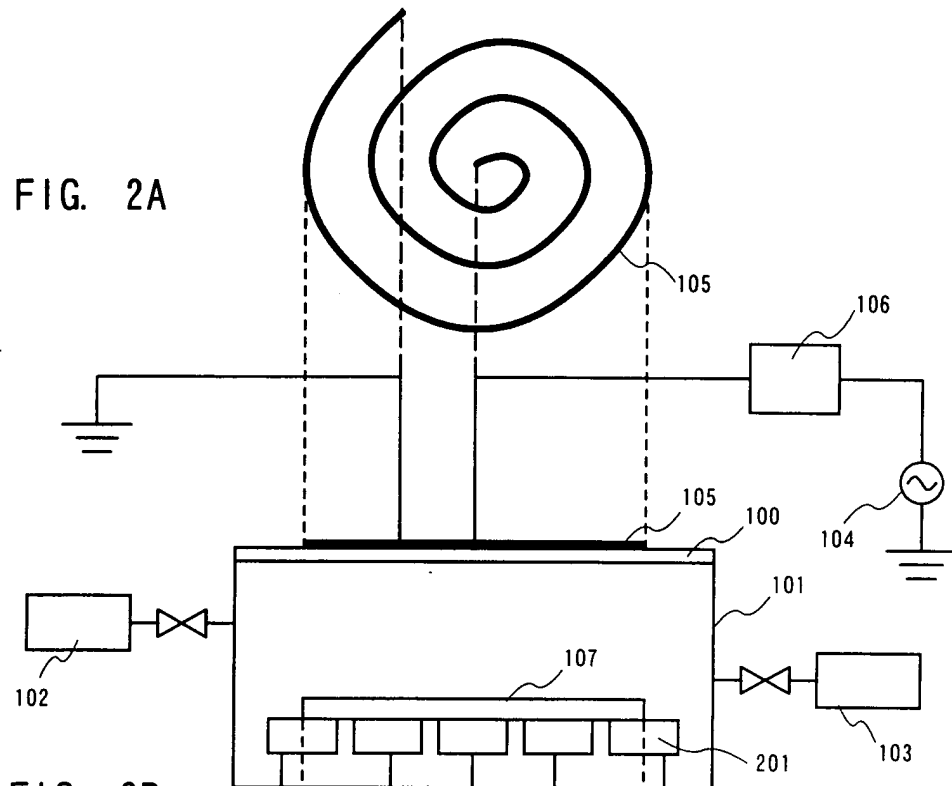


FIG. 2B

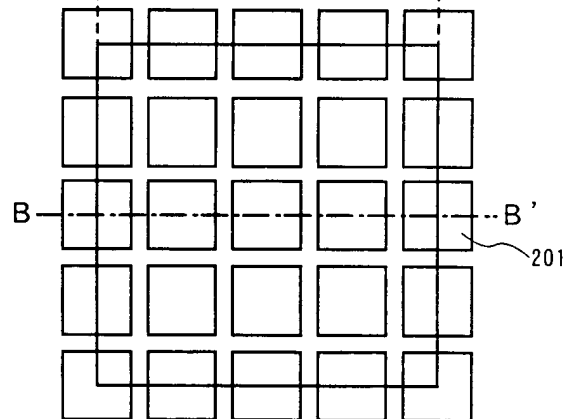


FIG. 2C

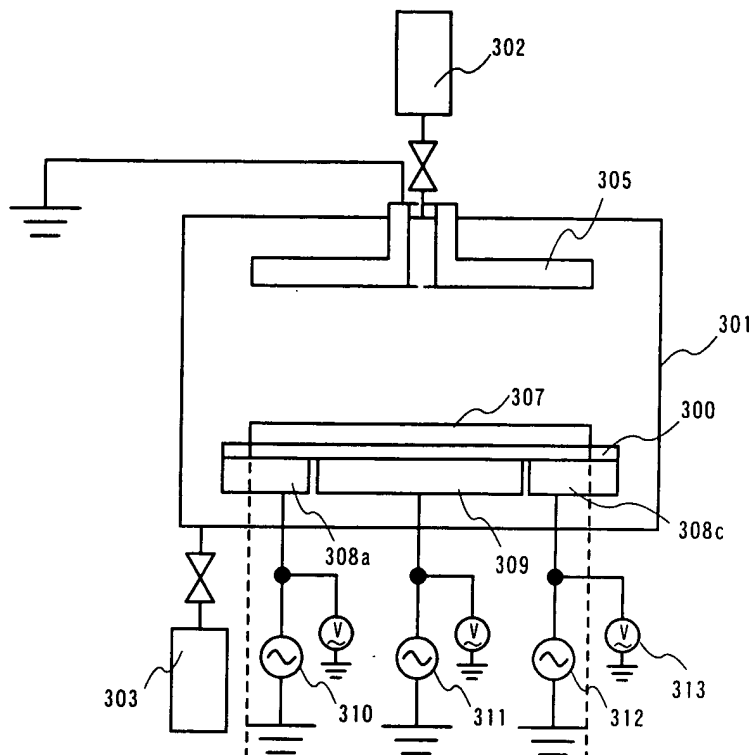


FIG. 3A

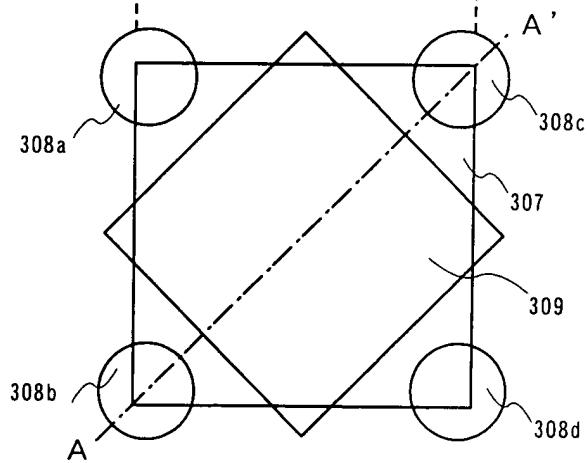


FIG. 3B

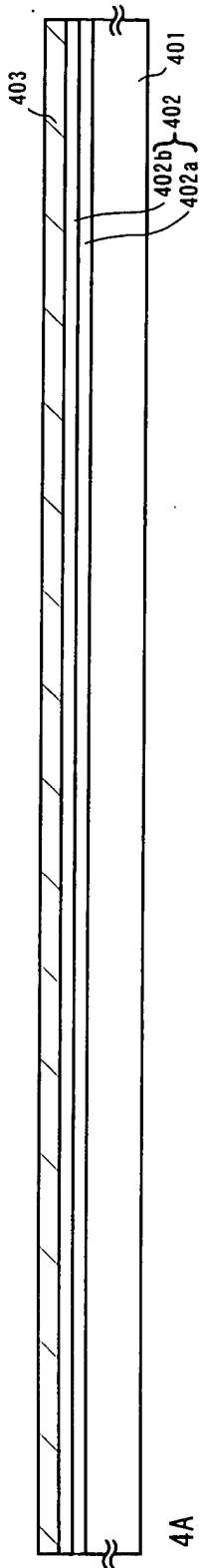


FIG. 4A



FIG. 4B

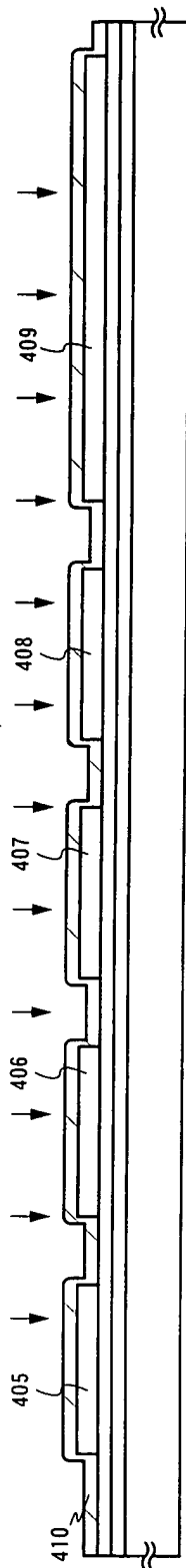


FIG. 4C

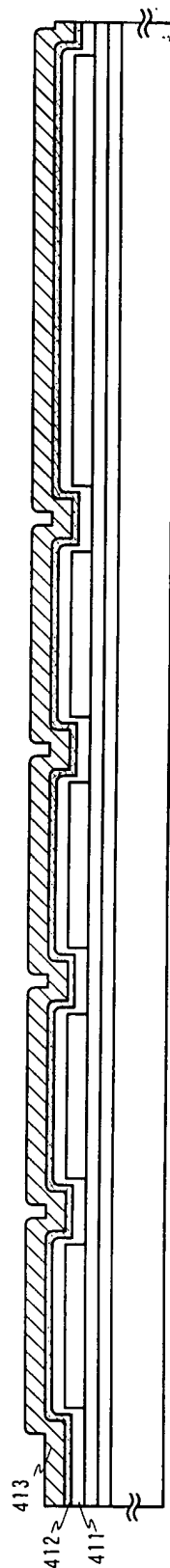


FIG. 4D

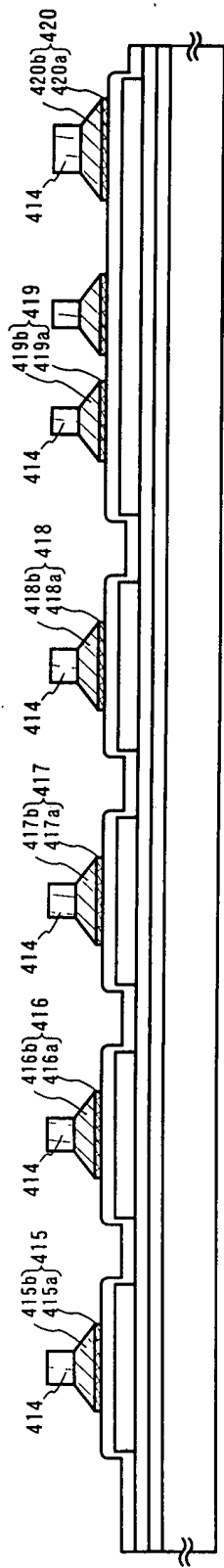


FIG. 5A

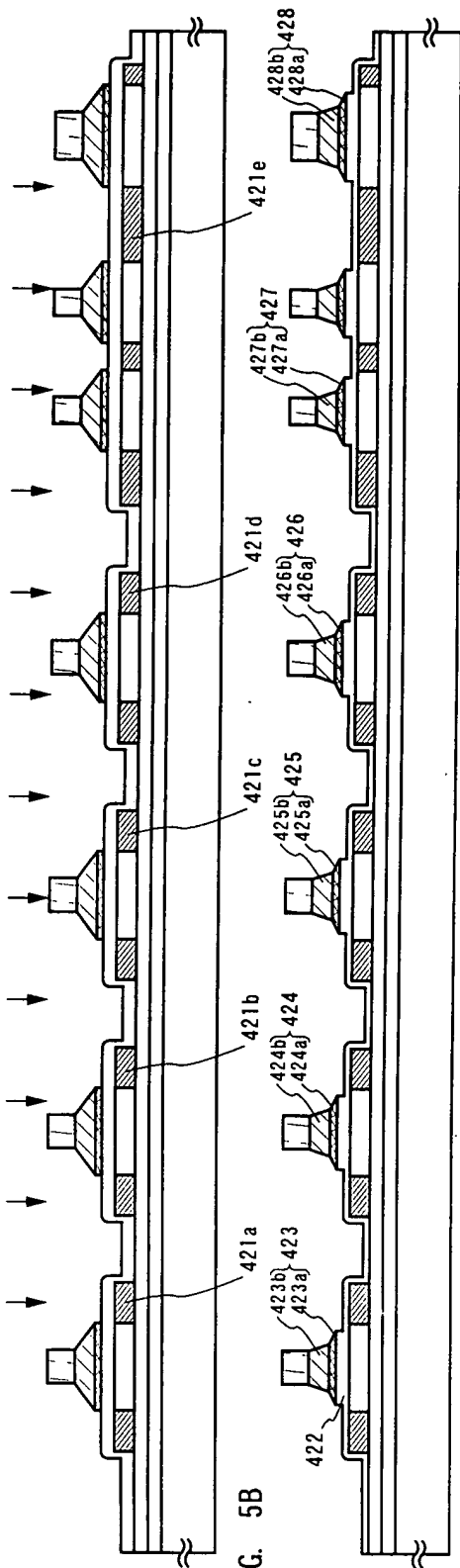


FIG. 5B

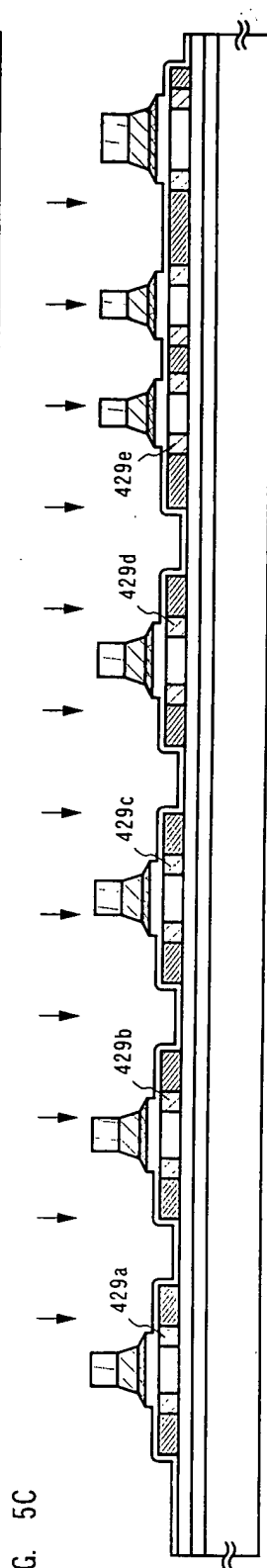


FIG. 5C

FIG. 5D

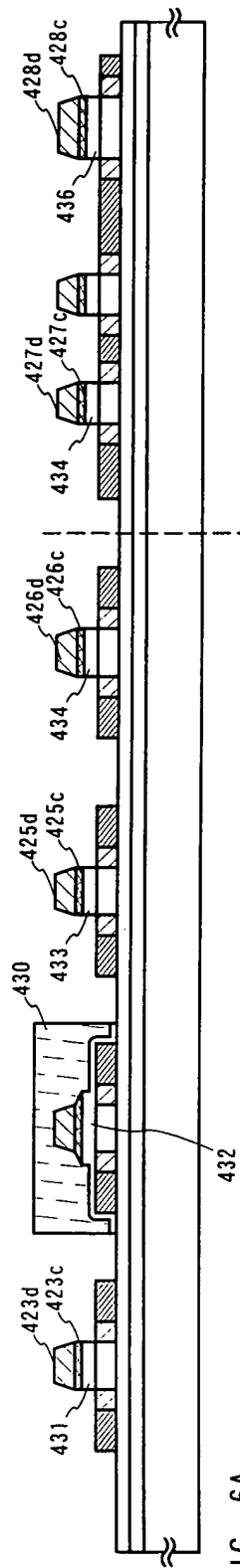


FIG. 6A

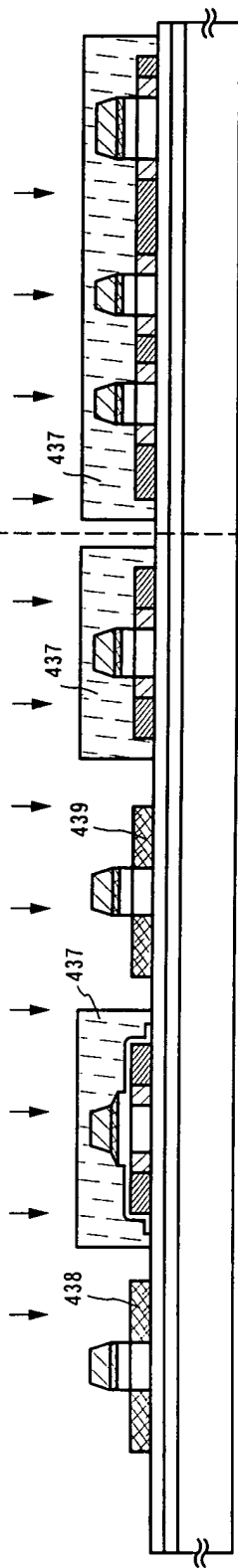


FIG. 6B

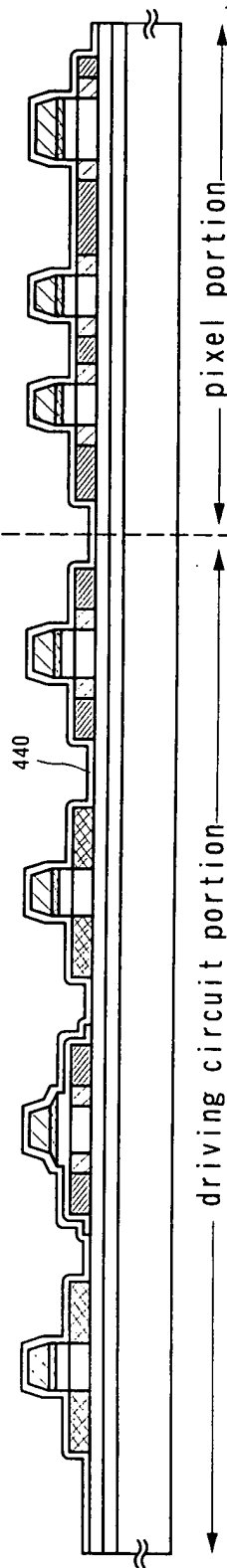


FIG. 6C

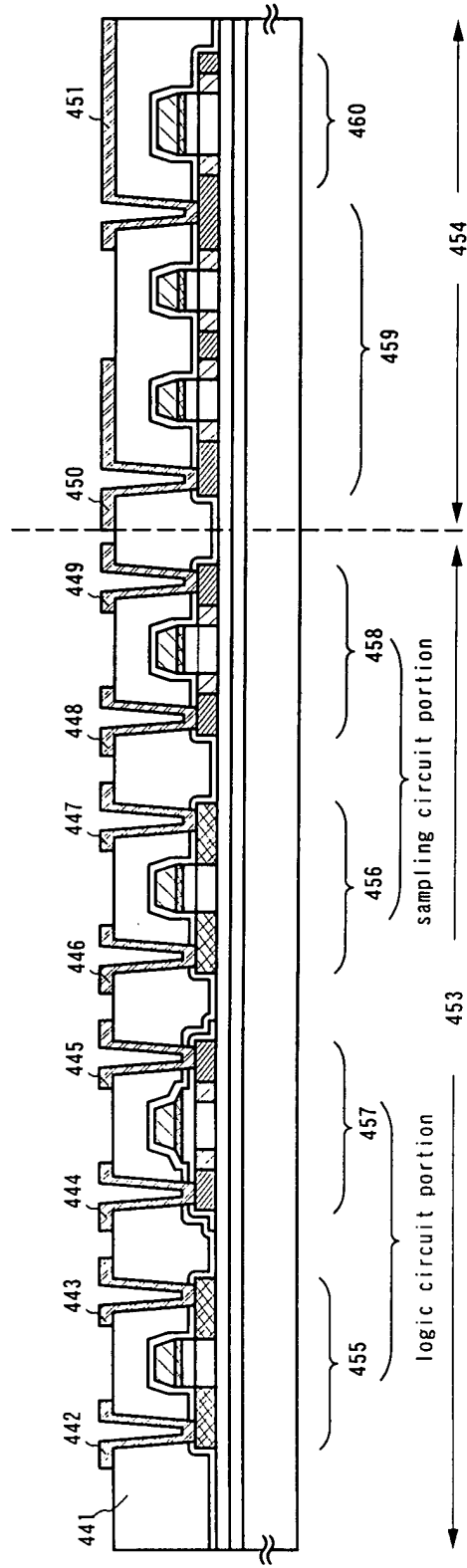


FIG. 7

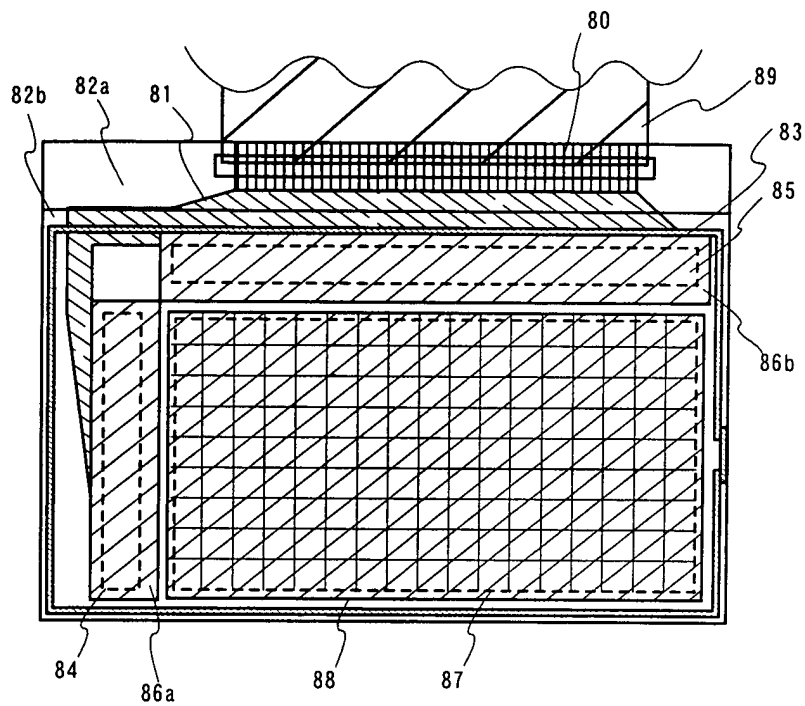


FIG. 8



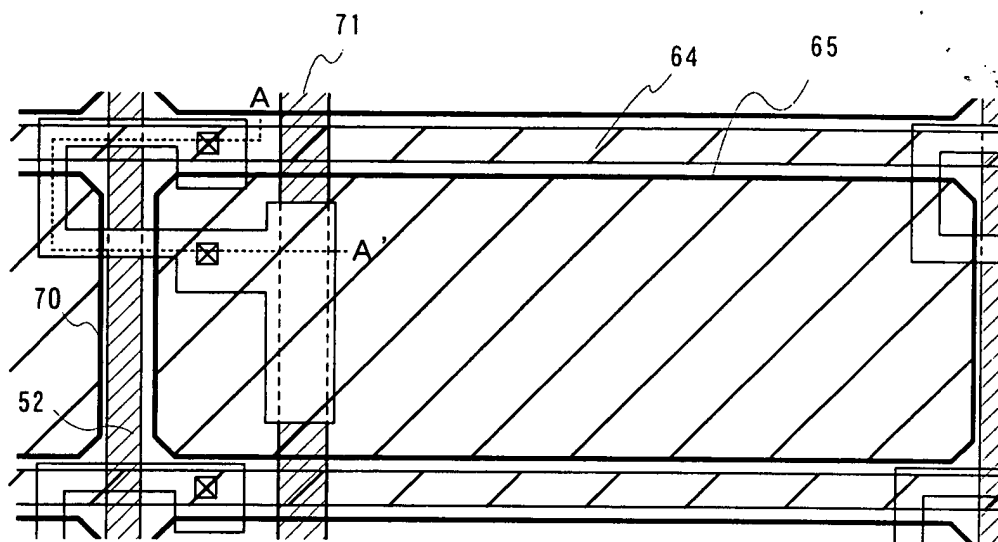


FIG. 9A

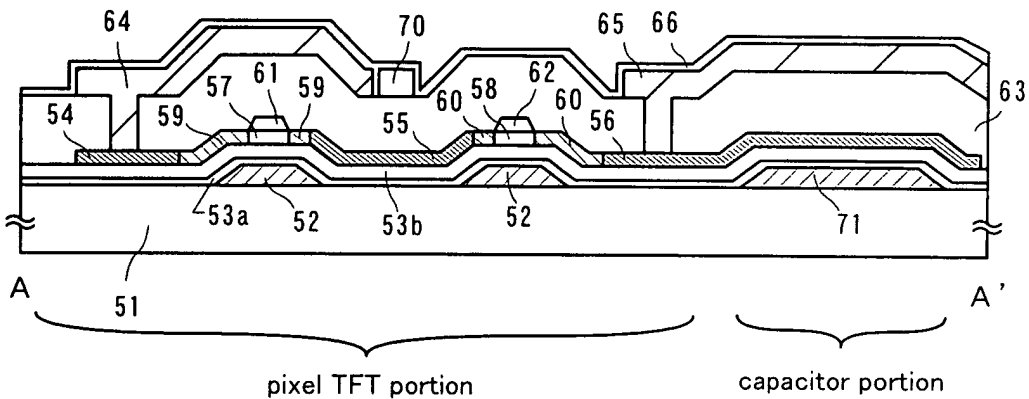


FIG. 9B

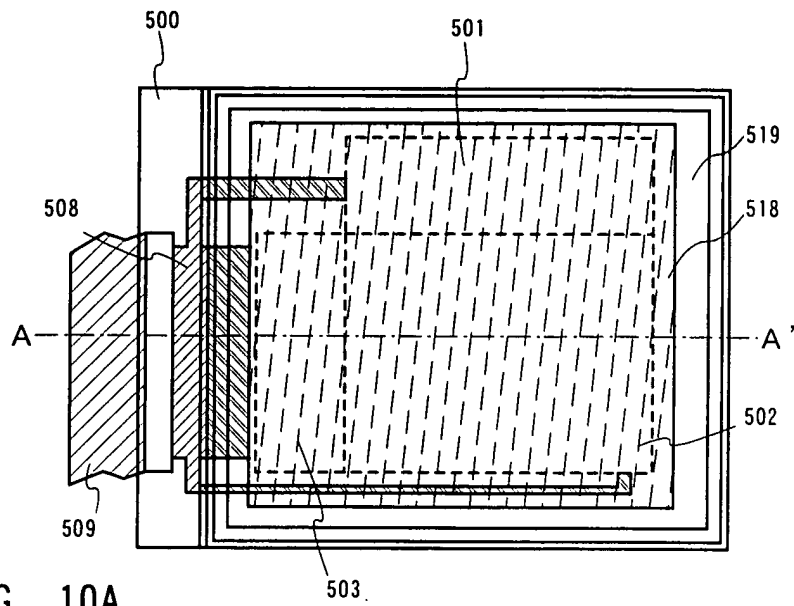


FIG. 10A

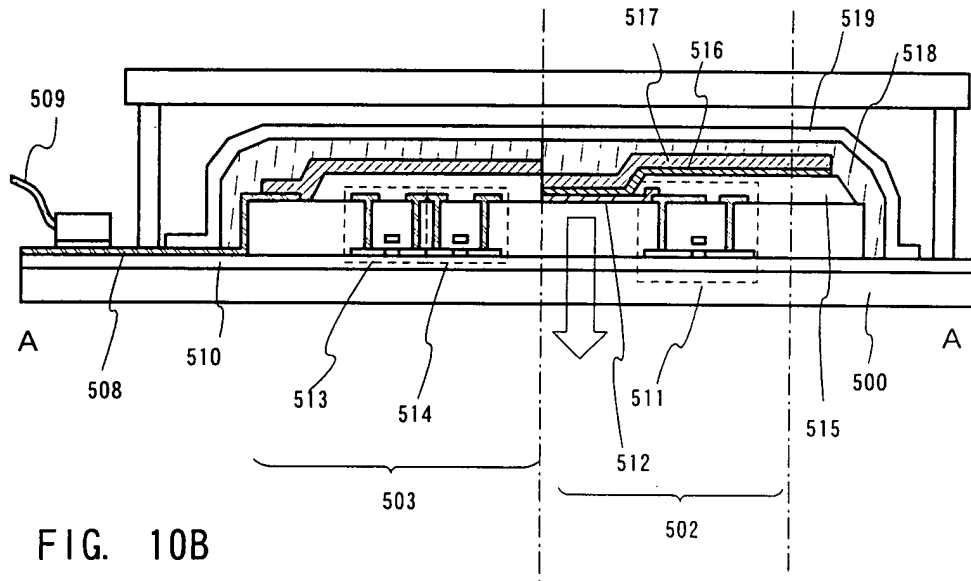


FIG. 10B

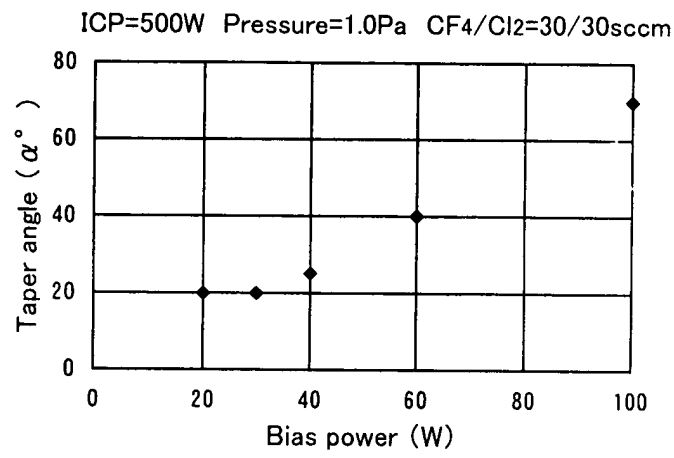


FIG. 11 Dependence of taper angle on bias power.

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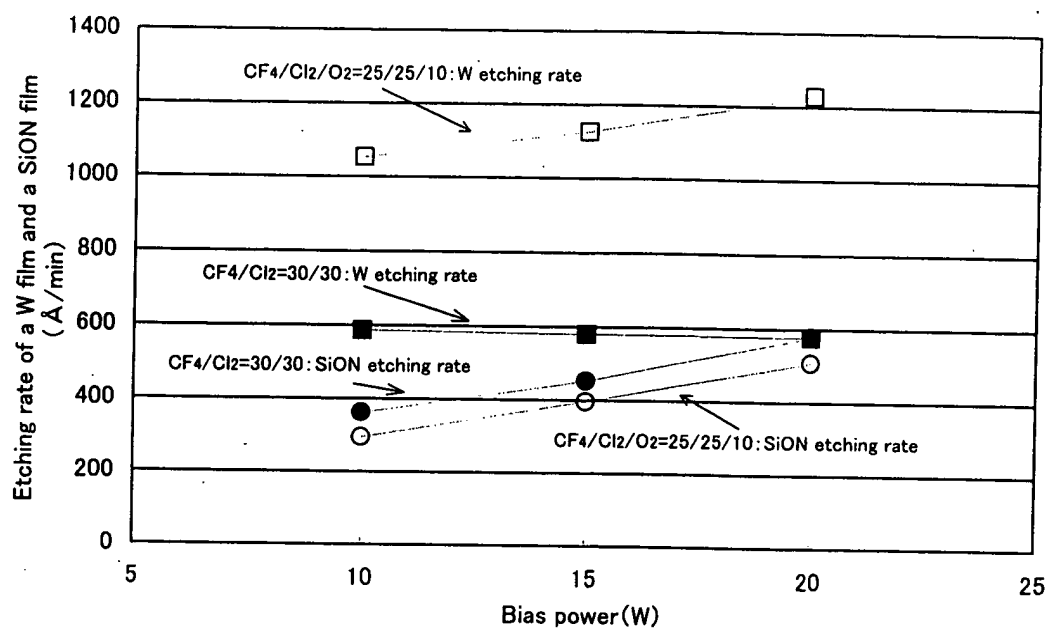


Fig. 12 Dependence of an etching rate of a W film and an SiON film on bias power.

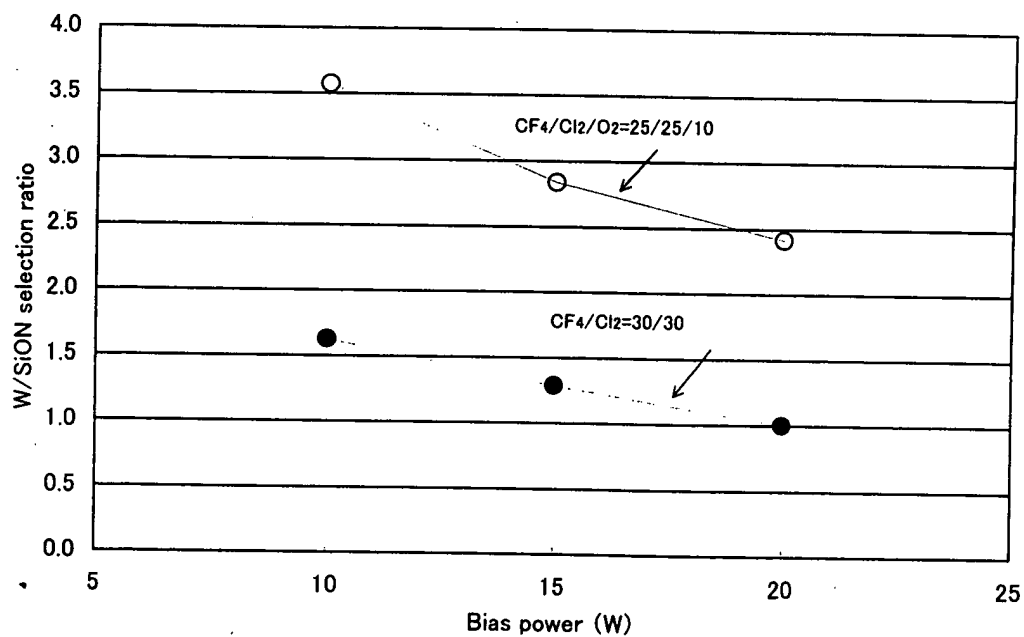


Fig. 13 Dependence of a selection ratio between a W film and an SiON film on a bias power.

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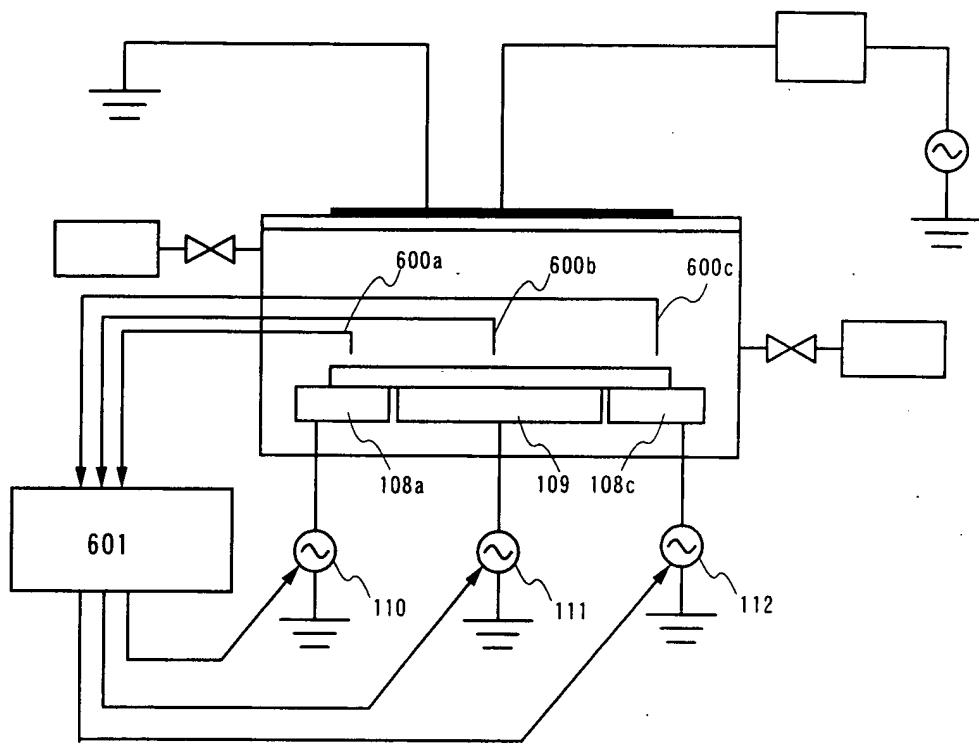


FIG. 14

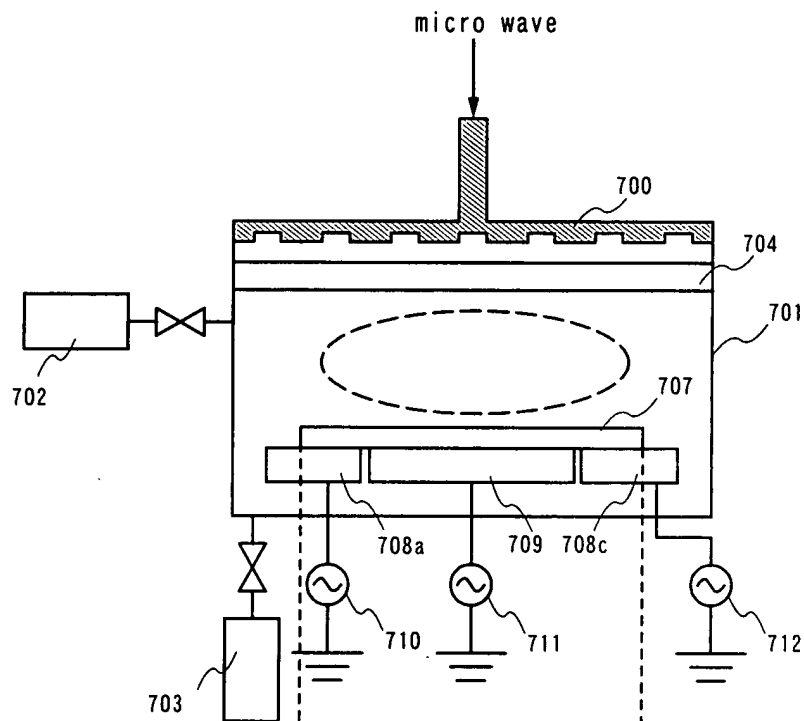


FIG. 15A

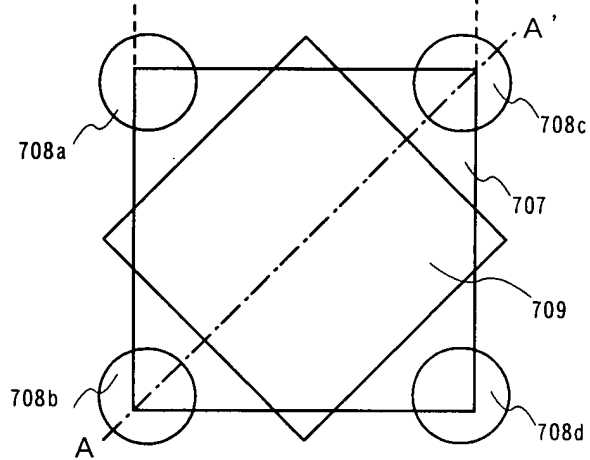


FIG. 15B

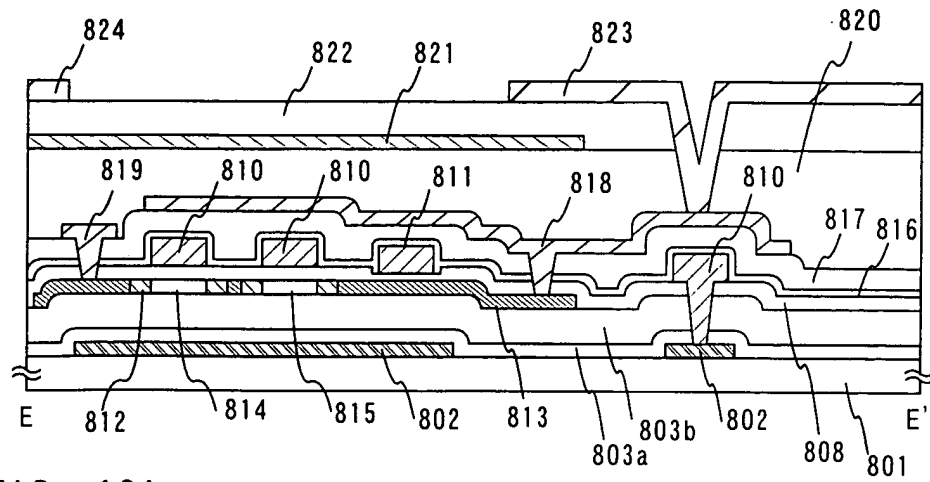


FIG. 16A

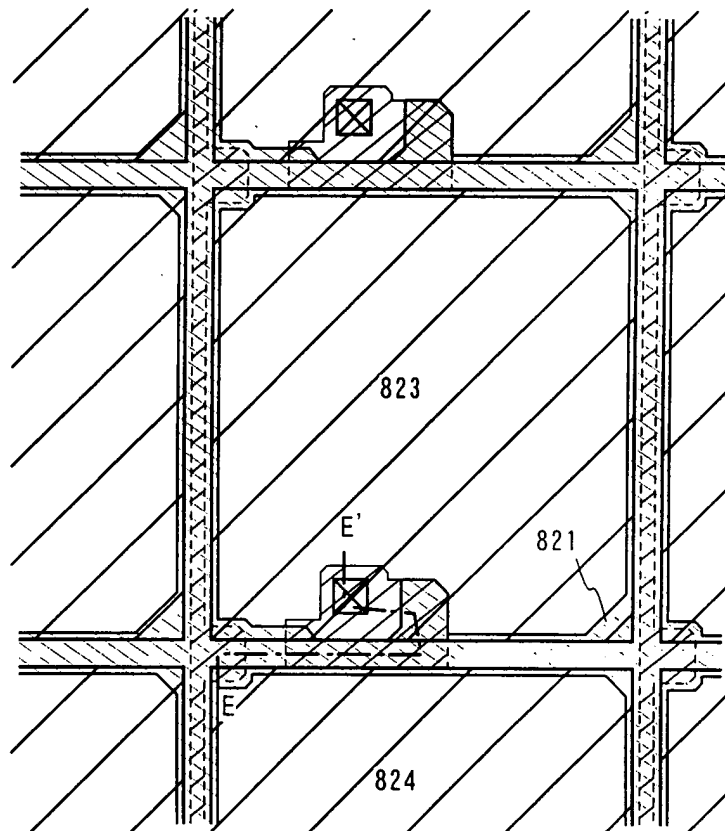


FIG. 16B

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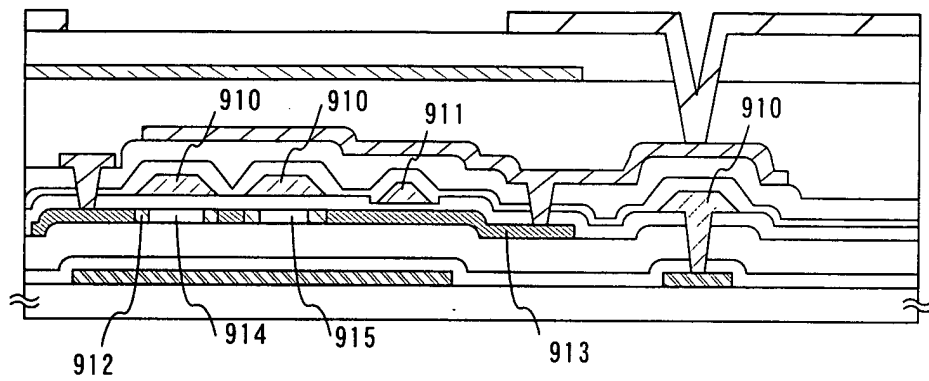


FIG. 17



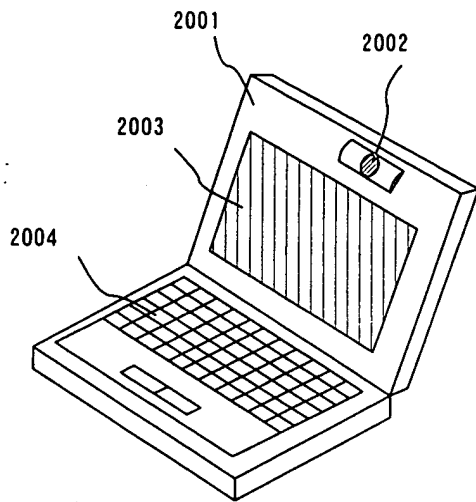


FIG. 18A

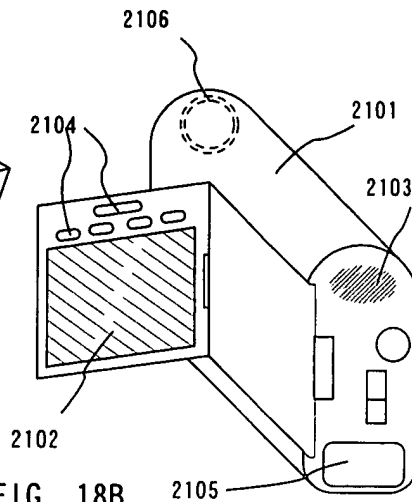


FIG. 18B

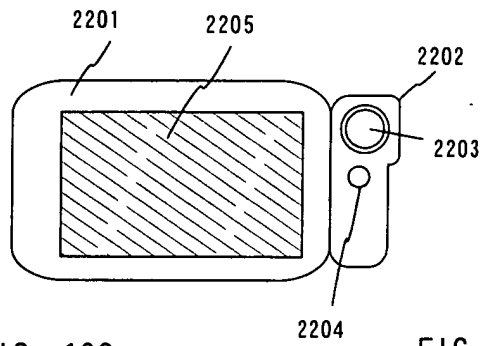


FIG. 18C

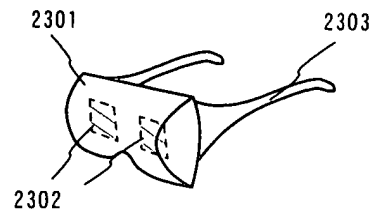


FIG. 18D

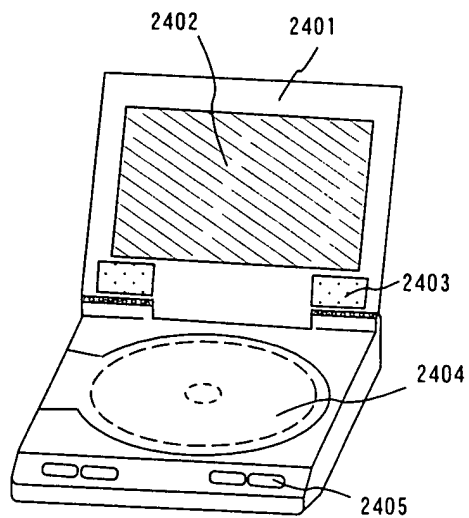


FIG. 18E

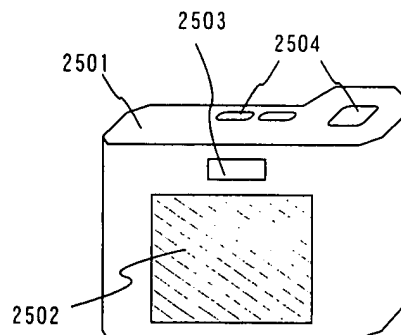


FIG. 18F

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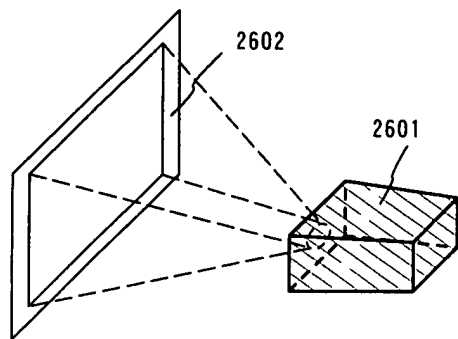


FIG. 19A

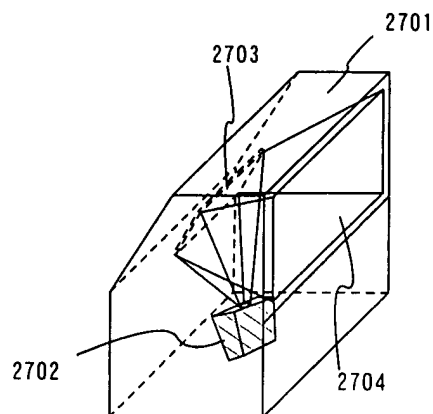


FIG. 19B

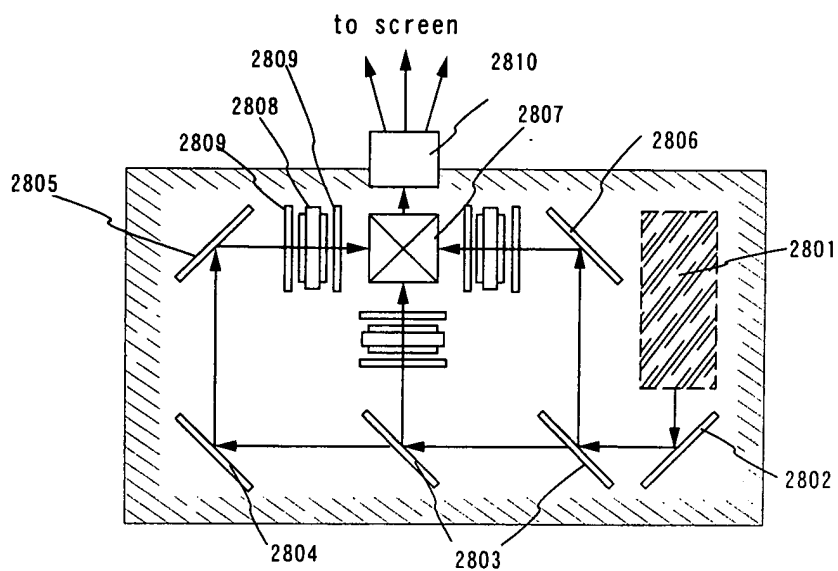


FIG. 19C

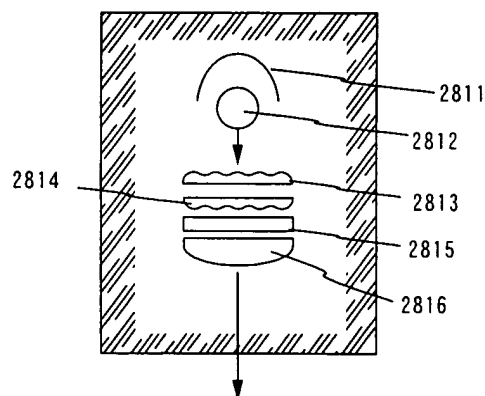


FIG. 19D

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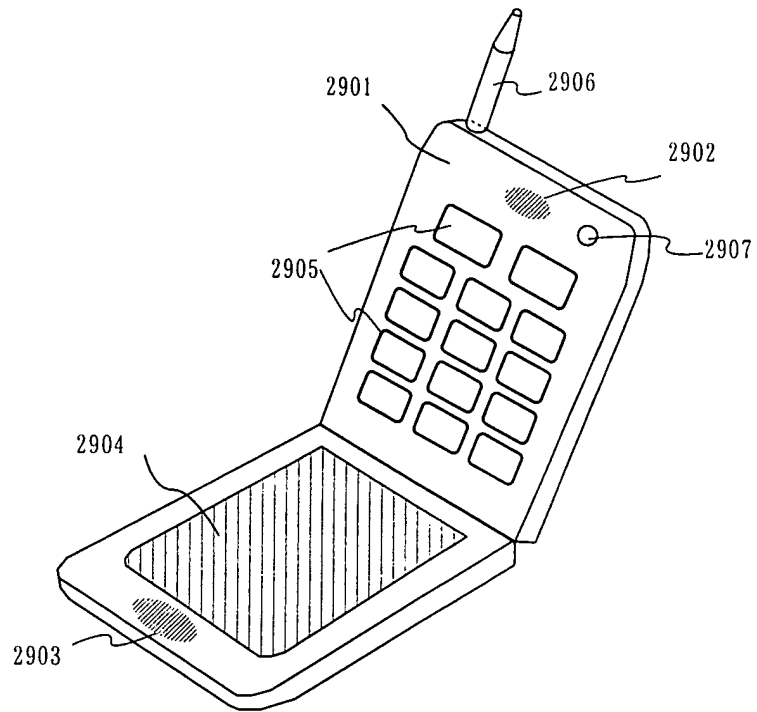


FIG. 20A

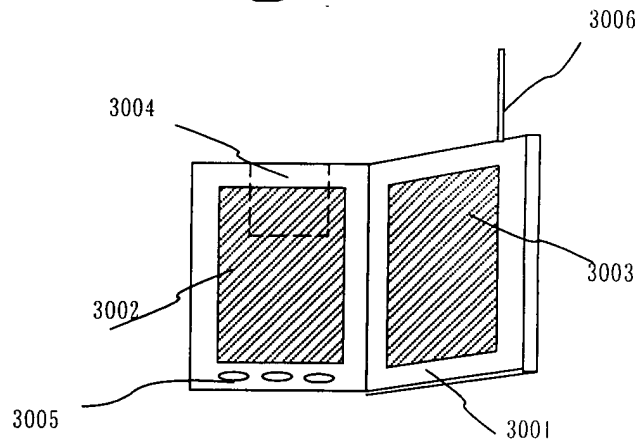


FIG. 20B

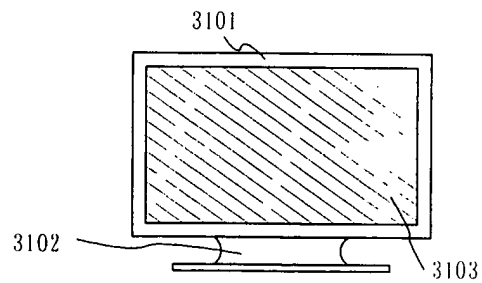


FIG. 20C

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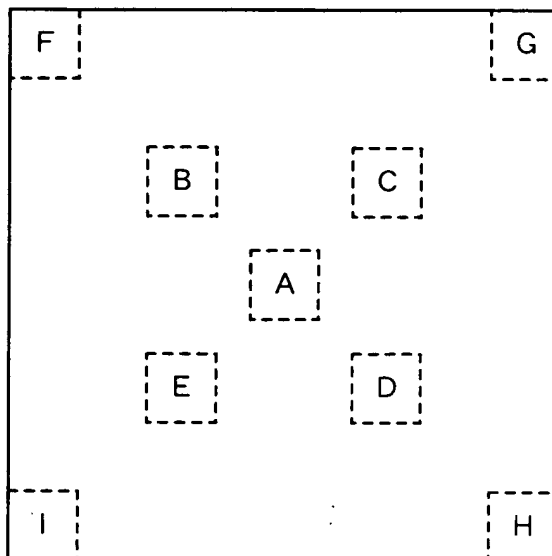


FIG. 21A

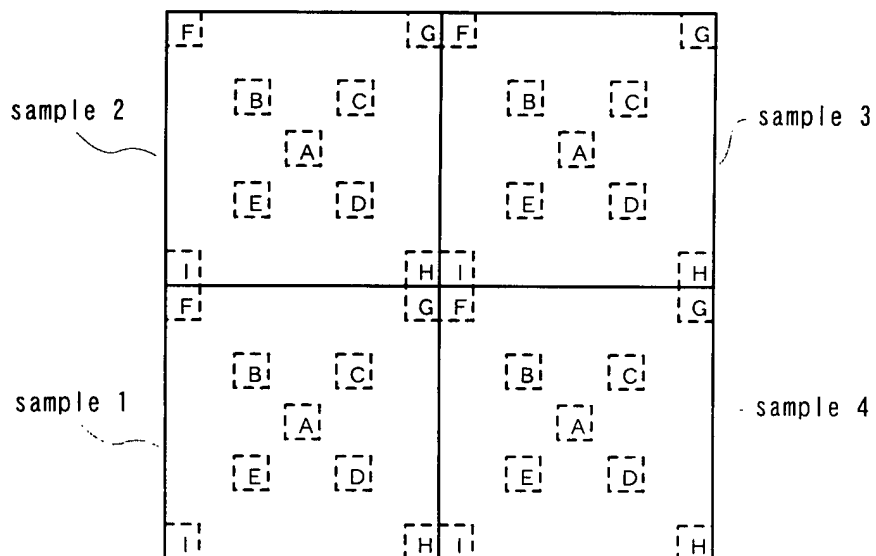


FIG. 21B